Silicon NPN Power Transistors 2SD1197

DESCRIPTION

·With TO-3PN package
·High DC current gain.
·Large current capacity and wide ASO.
·Low saturation voltage
·DARLINGTON
·Complement to type 2SB887

APPLICATIONS

·Motor drivers, printer hammer drivers, relay drivers,voltage regulator control.

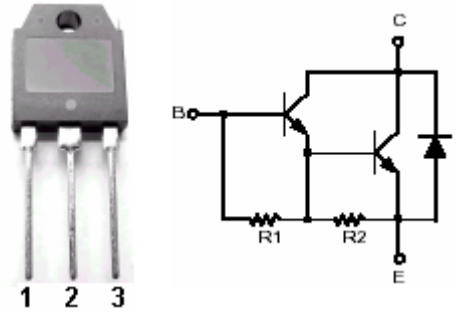

Fig.1 simplified outline (TO-3PN) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	110	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		10	A
I_{CP}	Collector current (Pulse)		15	A
P_C	Collector power dissipation	T_C=25□	70	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;R_{BE}=∞	100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=5mA ;I_E=0	110			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A; I_B=10mA		0.9	1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A; I_B=10mA			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=80V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			3.0	mA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=3V	1500	4000		
f_T	Transition frequency	I_C=5A ; V_{CE}=5V		20		MHz

PACKAGE OUTLINE

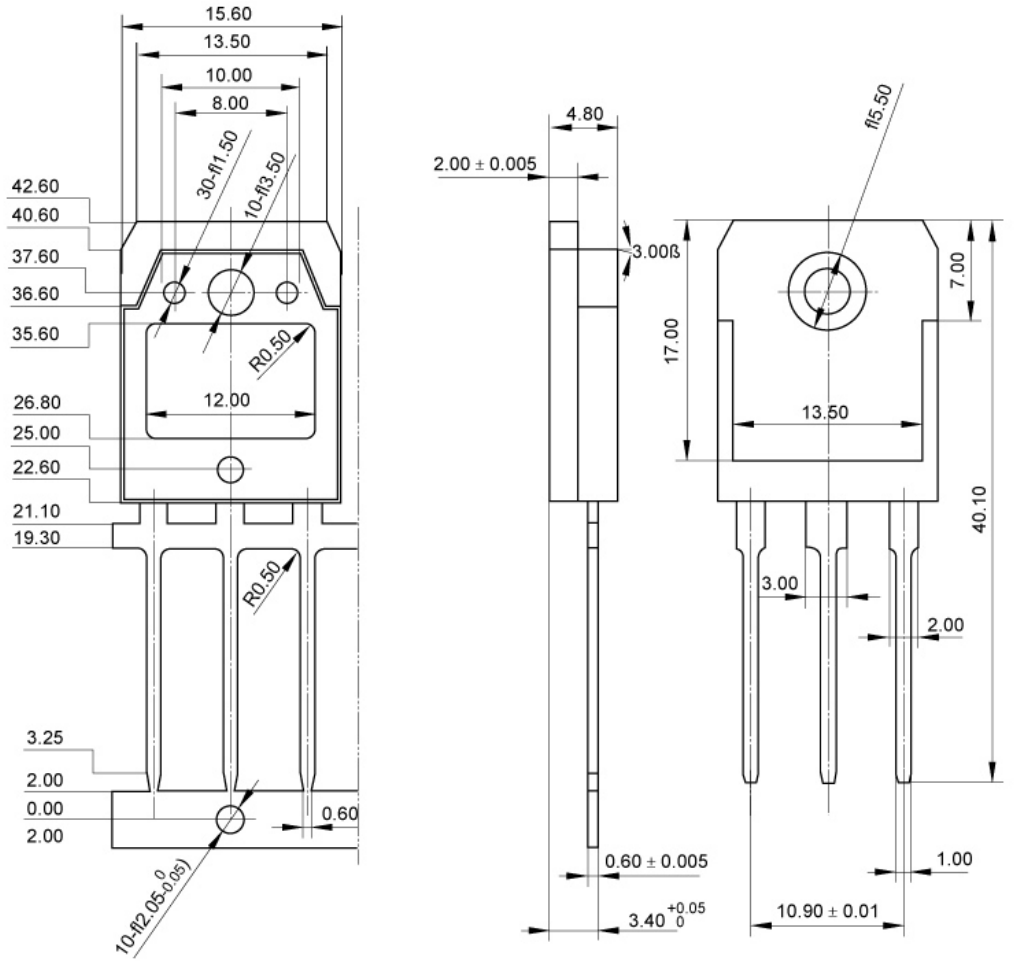

Fig.2 outline dimensions